FIG. 1

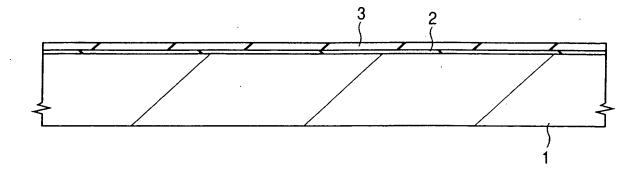


FIG. 2

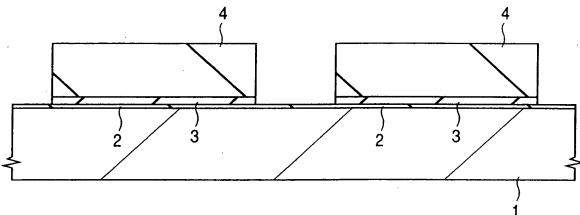
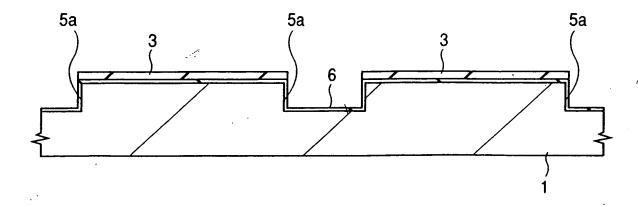


FIG. 3



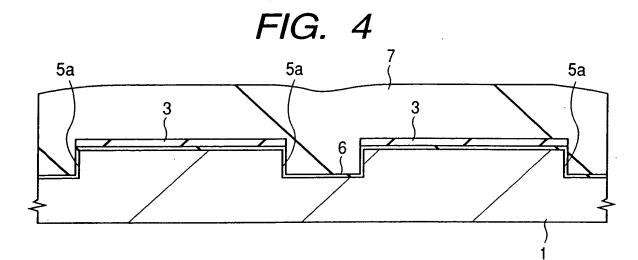


FIG. 5

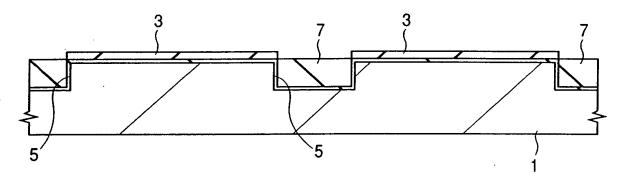


FIG. 6

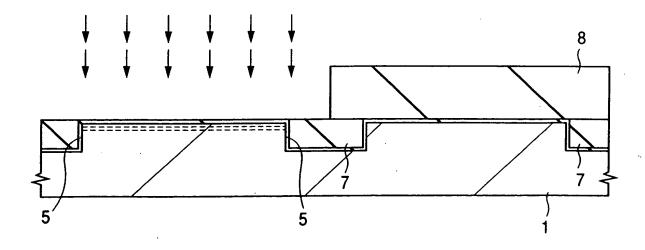


FIG. 7

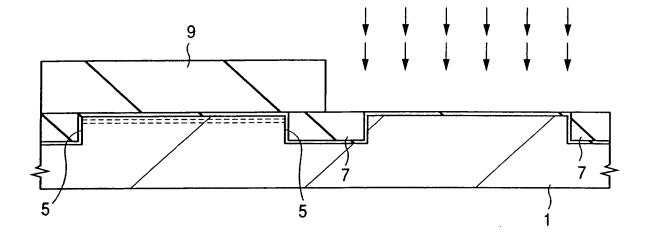


FIG. 8

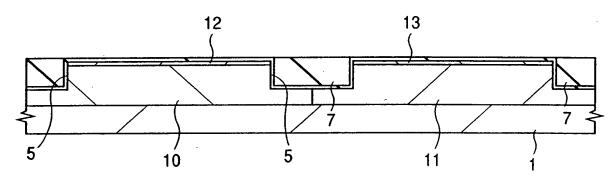
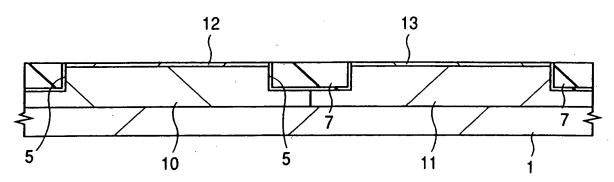


FIG. 10



)

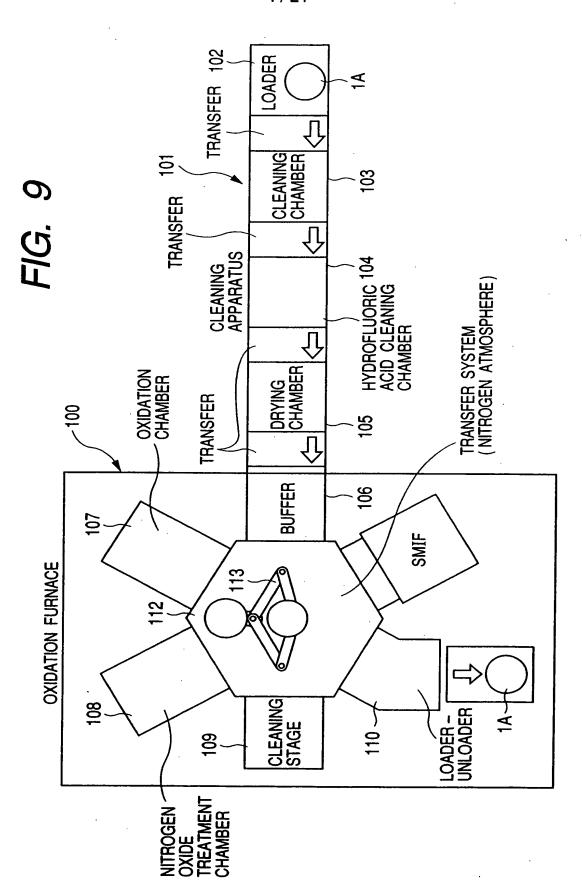
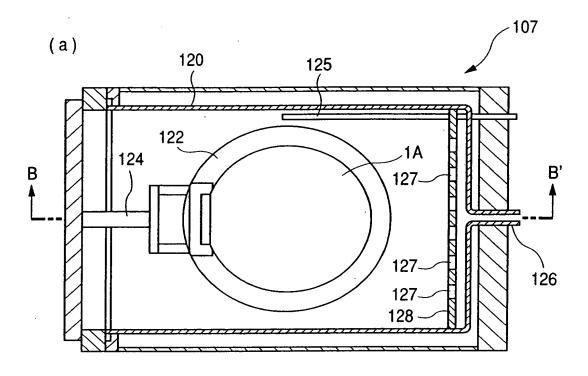


FIG. 11



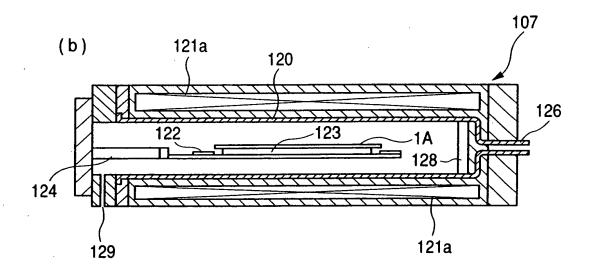
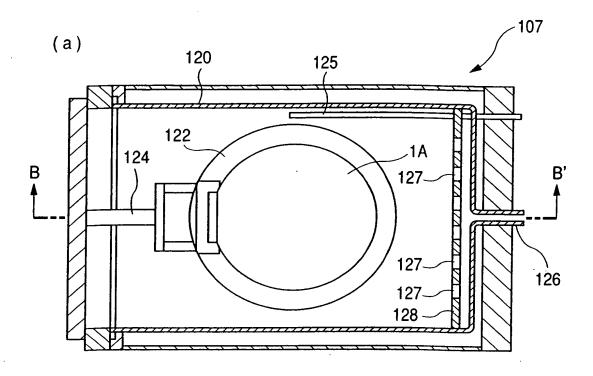
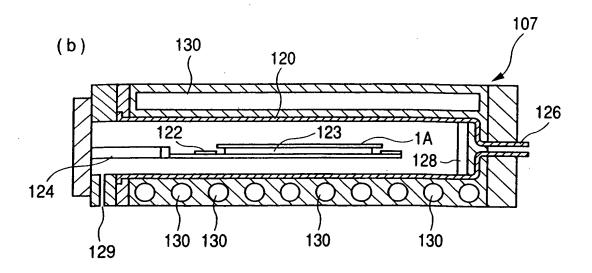
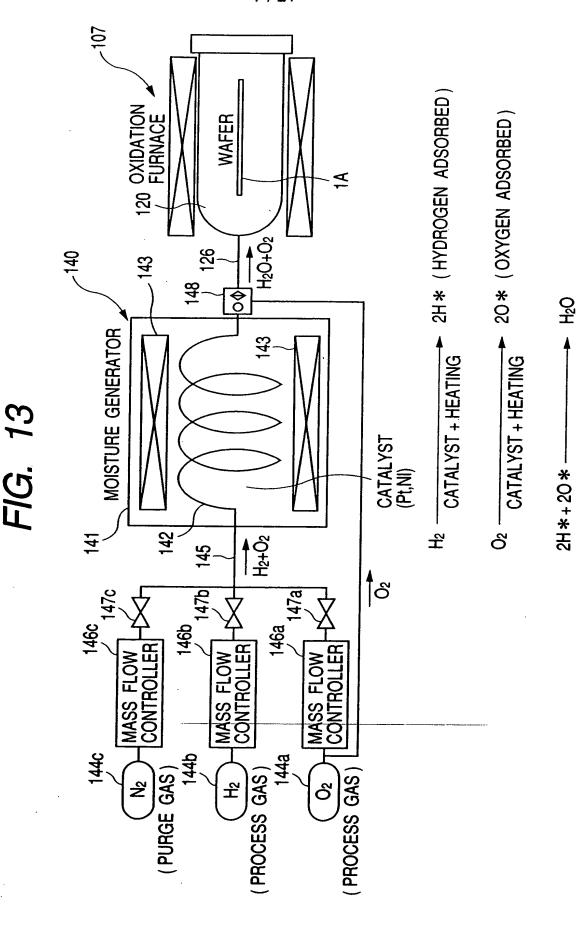


FIG. 12







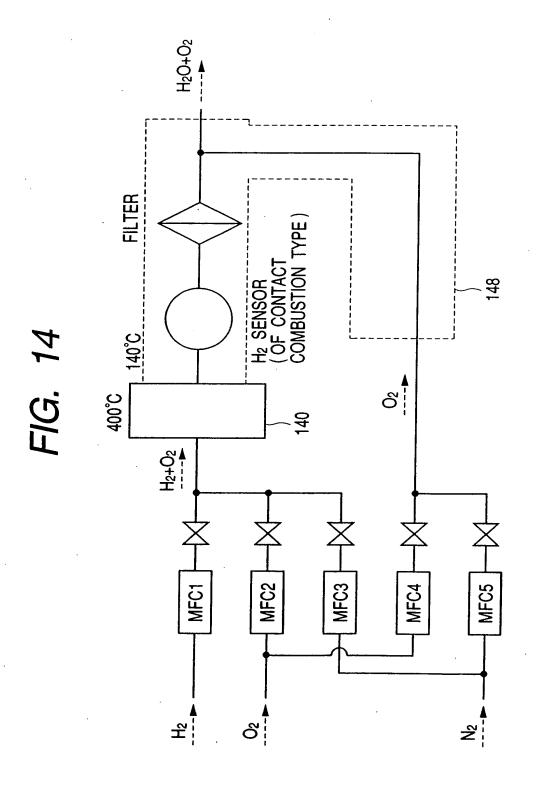


FIG. 15	WAFER	55,,								
	AFTER- PURGE	2, 20,,								
	OXIDATION	ດໃ								
	H ₂ INTRODUCTION	15"								
	O ₂ PURGE	0 – 55"								
	N ₂ PURGE	1,								
	WAFER LOAD	55"								
		TIME	2	FLOW	O ₂ FLOW RATE			H ₂ FLOW RATE		

()()

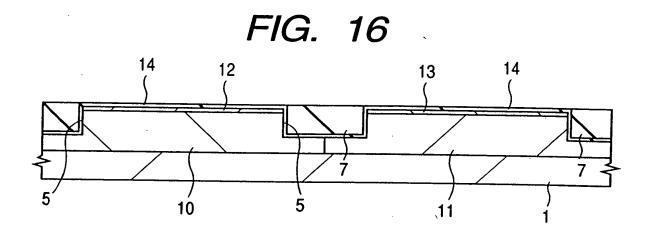


FIG. 17

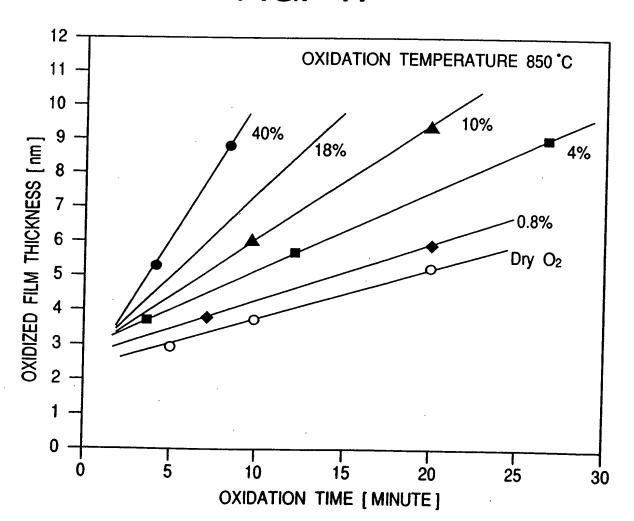
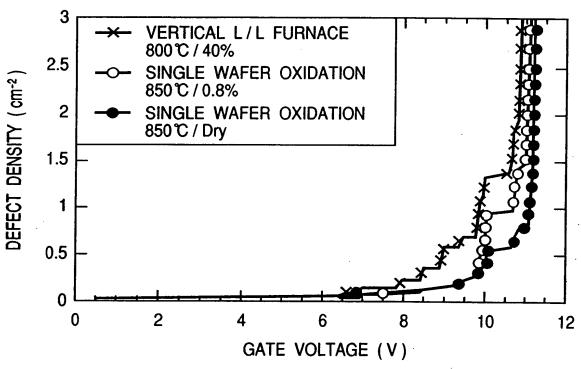


FIG. 18



INITIAL WITHSTAND VOLTAGE OF LOW MOISTURE CONTENT OXIDE FILM (OXIDE FILM THICKNESS = 9nm,S = 0.19cm²)

FIG. 19

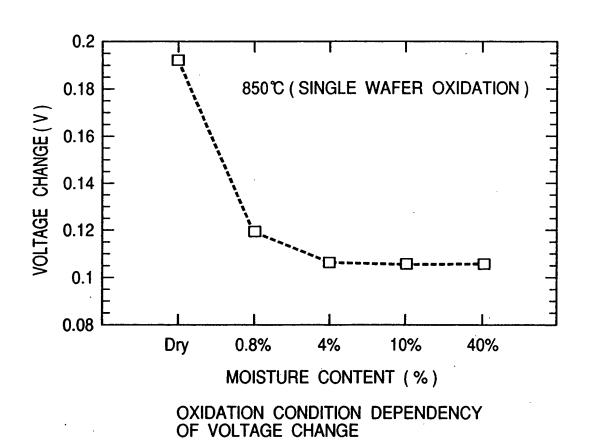
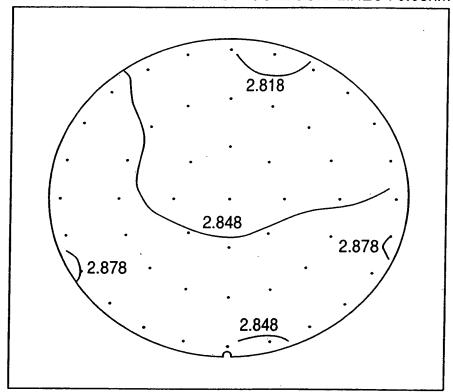


FIG. 20





WAFER DIAMETER: 8 inch

AVERAGE: 2.848 [nm]

MAX.: 2.881 [nm]

MIN.: 2.814 [nm]

MAX. – MIN. : 0.067 [nm]

±1.18[%]

TREATING CONDITIONS: 850°C, 2'30"

 $H_2/O_2: 0.05/4.9 \text{slm}$ (MOISTURE CONTENT: 0.8%) MEASUREMENT: AT 49 POINTS BY ELLIPSOMETER

()()

FIG. 21

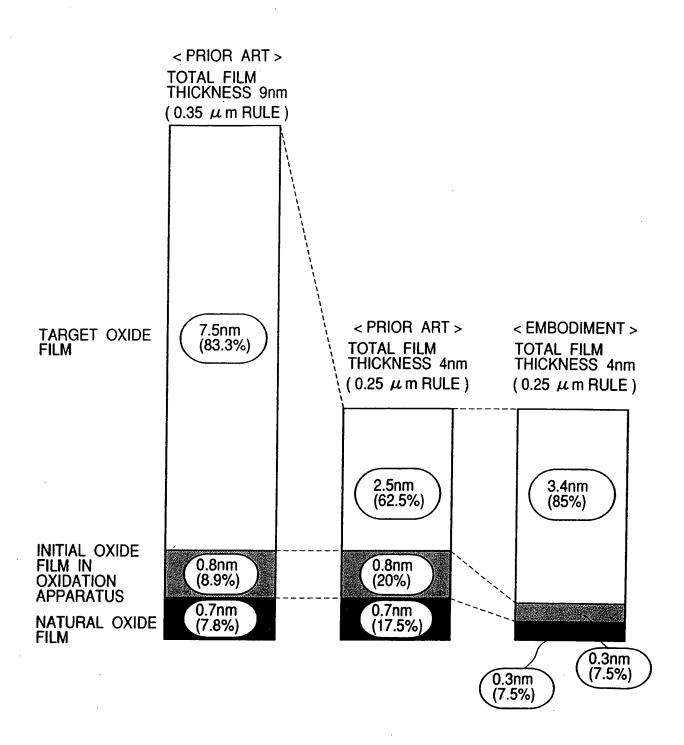
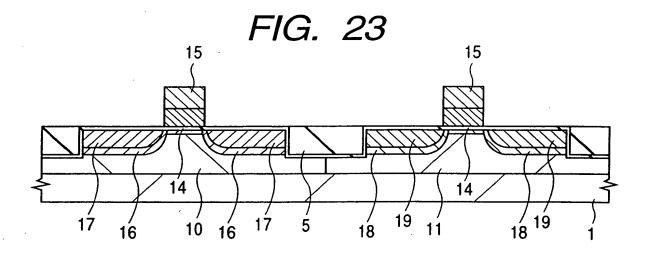


FIG. 22

15
14
7
7
11
11
11



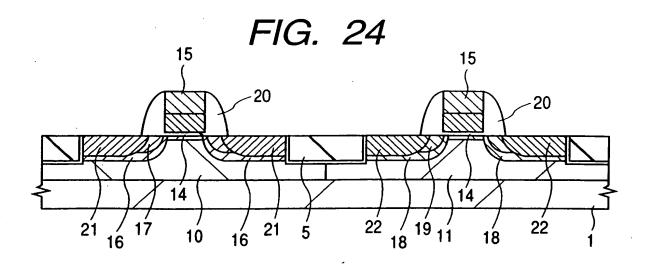


FIG. 25

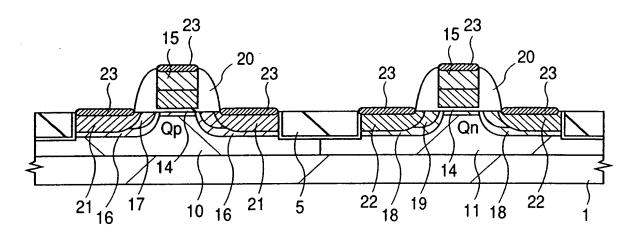


FIG. 26

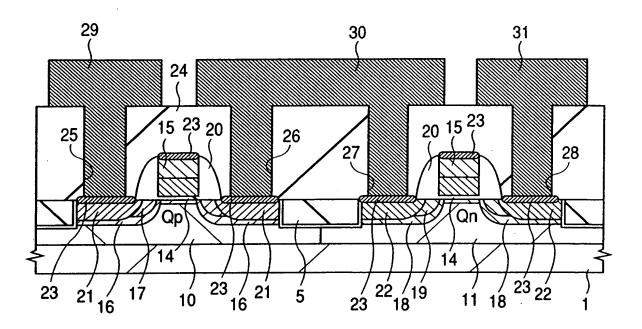


FIG. 27

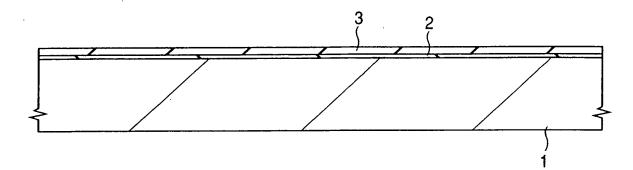


FIG. 28

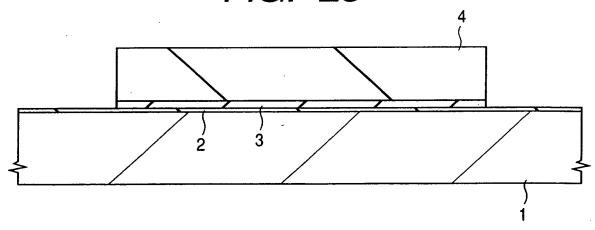


FIG. 29

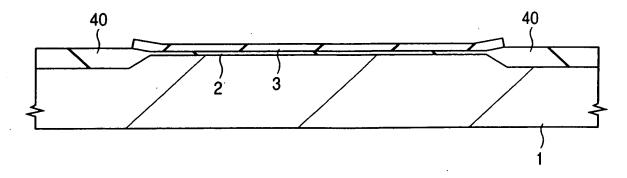
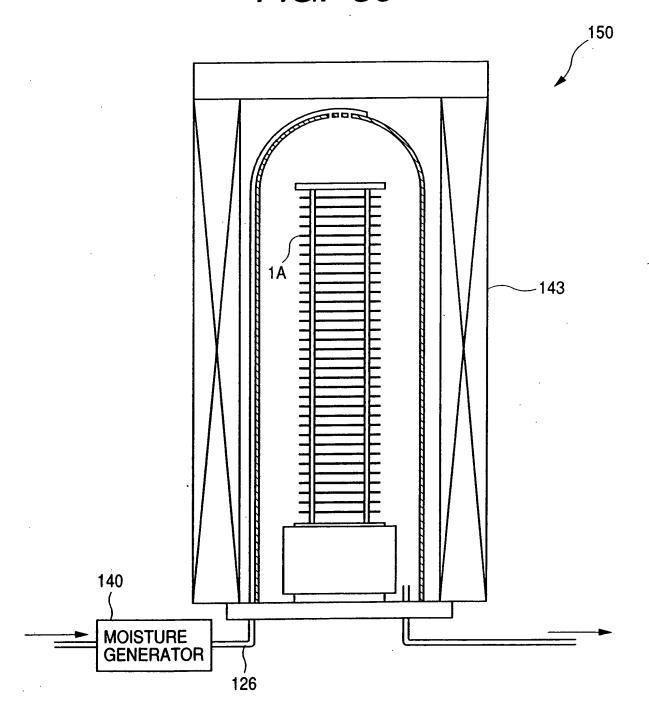


FIG. 30



WAFER UNLOAD **1**0, AFTER-Purge 2, 20,, ARBITRARY (SEVERAL MINS.) OXIDATION FIG. 31 H₂ INTRODUCTION 5 O₂ PURGE ດີ N₂ Purge WAFER LOAD 9 N₂ FLOW RATE O₂ FLOW RATE H2 FLOW RATE TIME

(-)(-)

FIG. 32

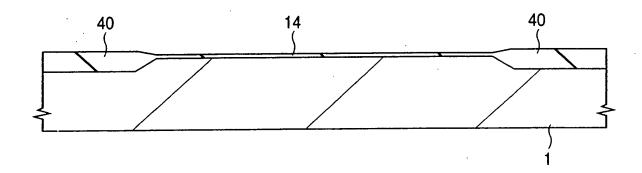


FIG. 34

